

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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APPLICANT
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GROUP
2822

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<u>KBP</u>		US 6,017,608	01/2000	Wang et al.	
<u>KBP</u>		US 5,868,930	02/1999	Saida et al.	
		US			
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<u>KBP</u>		S. NAKAYAMA, "The effect of nitrogen in P + polysilicon gates on boron penetration into silicon substrate through the gate oxide", Symposium on VLSI technology Digest of Technical papers, pages 228-229, January 1996.
<u>KBP</u>		T. KUROI et al., "Novel NICE (Nitrogen Implantation into CMOS Gate Electrode and Source-Drain) Structure for High Reliability and High Performance 0.25 um Dual Gate CMOS", IEDM, pages 325-328, January 1996.

EXAMINER

DATE CONSIDERED

*EXAMINER Initial if reference considered whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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